

Gun Hee Kim

List of Publications by Year in descending order

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37
papers

2,182
citations

361296

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h-index

360920

35
g-index

37
all docs

37
docs citations

37
times ranked

1979
citing authors

#	ARTICLE	IF	CITATIONS
1	Structural, electrical, and optical properties of p-type ZnO thin films with Ag dopant. Applied Physics Letters, 2006, 88, 202108.	1.5	213
2	Effect of indium composition ratio on solution-processed nanocrystalline InGaZnO thin film transistors. Applied Physics Letters, 2009, 94, .	1.5	200
3	Formation Mechanism of Solution-Processed Nanocrystalline InGaZnO Thin Film as Active Channel Layer in Thin-Film Transistor. Journal of the Electrochemical Society, 2009, 156, H7.	1.3	187
4	Inkjet-printed InGaZnO thin film transistor. Thin Solid Films, 2009, 517, 4007-4010.	0.8	153
5	Influence of thermal annealing ambient on Ga-doped ZnO thin films. Journal of Crystal Growth, 2007, 309, 128-133.	0.7	137
6	Investigation of the effects of Mg incorporation into InZnO for high-performance and high-stability solution-processed thin film transistors. Applied Physics Letters, 2010, 96, .	1.5	136
7	Investigating addition effect of hafnium in InZnO thin film transistors using a solution process. Applied Physics Letters, 2010, 96, .	1.5	131
8	Synthesis and analysis of Ag-doped ZnO. Journal of Applied Physics, 2006, 100, 093701.	1.1	127
9	Investigation on doping dependency of solution-processed Ga-doped ZnO thin film transistor. Applied Physics Letters, 2008, 93, .	1.5	114
10	Investigation on the p-type formation mechanism of arsenic doped p-type ZnO thin film. Applied Physics Letters, 2006, 89, 181103.	1.5	108
11	Electrical, structural, and optical properties of ITO thin films prepared at room temperature by pulsed laser deposition. Applied Surface Science, 2006, 252, 4834-4837.	3.1	96
12	Electrical characteristics of solution-processed InGaZnO thin film transistors depending on Ga concentration. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1677-1679.	0.8	84
13	High Electrical Performance of Wet-Processed Indium Zinc Oxide Thin-Film Transistors. IEEE Electron Device Letters, 2010, 31, 311-313.	2.2	68
14	The effect of La in InZnO systems for solution-processed amorphous oxide thin-film transistors. Applied Physics Letters, 2010, 97, .	1.5	59
15	Carrier-suppressing effect of scandium in InZnO systems for solution-processed thin film transistors. Applied Physics Letters, 2010, 97, .	1.5	54
16	Characteristics of gravure printed InGaZnO thin films as an active channel layer in thin film transistors. Thin Solid Films, 2010, 518, 6249-6252.	0.8	49
17	Investigation on doping behavior of copper in ZnO thin film. Microelectronics Journal, 2009, 40, 272-275.	1.1	45
18	Density-of-States Modeling of Solution-Processed InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2010, 31, 1131-1133.	2.2	42

#	ARTICLE	IF	CITATIONS
19	Electrical Properties of Yttrium-Indium-Zinc-Oxide Thin Film Transistors Fabricated Using the Sol-Gel Process and Various Yttrium Compositions. Japanese Journal of Applied Physics, 2010, 49, 03CB01.	0.8	39
20	Effects of Hf incorporation in solution-processed Hf-InZnO TFTs. Thin Solid Films, 2011, 519, 5740-5743.	0.8	37
21	Thin film transistors by solution-based indium gallium zinc oxide/carbon nanotubes blend. Thin Solid Films, 2009, 517, 4011-4014.	0.8	19
22	InGaZnO thin-film transistors with YHfZnO gate insulator by solution process. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1668-1671.	0.8	16
23	Growth of Transparent nc-InGaO ₃ (ZnO) ₂ Thin Films with Indium mol Ratios Using Solution Process. Journal of the Electrochemical Society, 2008, 155, H848.	1.3	14
24	P24: Fabrication of Solution Processed InGaZnO Thin Film Transistor for Active Matrix Backplane. Digest of Technical Papers SID International Symposium, 2008, 39, 1258-1261.	0.1	9
25	Solution-processed indium-zinc oxide with carrier-suppressing additives. Journal of Information Display, 2012, 13, 113-118.	2.1	7
26	Thermal activation effects on the stoichiometry of indium zinc oxide thin-film transistors. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1689-1693.	0.8	6
27	Nonvolatile memory characteristics of solution-processed oxide thin-film transistors using Ag nanoparticles. Thin Solid Films, 2011, 519, 5771-5774.	0.8	6
28	Fabrication of transparent nanocrystalline InGaO ₃ (ZnO) ₂ thin films using a solution process. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1660-1663.	0.8	5
29	Origin of Device Performance Degradation in InGaZnO Thin-Film Transistors after Crystallization. Japanese Journal of Applied Physics, 2012, 51, 015601.	0.8	5
30	P182L: Late News Poster: Improvements in the Device Performance of Amorphous Indium Gallium Zinc Oxide Thin Film Transistors by XeCl Excimer Laser Irradiation. Digest of Technical Papers SID International Symposium, 2009, 40, 1170-1172.	0.1	4
31	P23: Solution-processed Amorphous Lanthanum Indium Zinc Oxide Thin-film Transistors. Digest of Technical Papers SID International Symposium, 2010, 41, 1308-1311.	0.1	4
32	Origin of Device Performance Degradation in InGaZnO Thin-Film Transistors after Crystallization. Japanese Journal of Applied Physics, 2012, 51, 015601.	0.8	3
33	Effect of Single-Walled Carbon Nanotube Concentration on the Electrical Properties of Solution-Based Indium Gallium Zinc Oxide Thin Film Transistors. Molecular Crystals and Liquid Crystals, 2009, 510, 87/[1221]-95/[1229].	0.4	2
34	Memory effects of all-solution-processed oxide thin-film transistors using ZnO nanoparticles. Journal of the Society for Information Display, 2011, 19, 404-409.	0.8	2
35	Blue photoluminescence of Si nanocrystallites embedded in silicon oxide. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 978-981.	0.9	1
36	Piezoelectric and dielectric properties of Pb(Zr,Ti)O ₃ -Pb(Mn,W,Sb,Nb)O ₃ with Ag ₂ O addition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 820-823.	0.9	0

#	ARTICLE	IF	CITATIONS
37	P&C22: Memory Effects of Solution&Circ;processed Oxide Thin&Circ;Film Transistor using ZnO Nanoparticles. Digest of Technical Papers SID International Symposium, 2010, 41, 1304-1317.	0.1	0